EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	369	(oxidiz$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:05
S2	326	(oxidiz$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold$4 or arm or support)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:22
S3	54	(oxidiz$4 near9 (layer or film)) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold$4 or arm or support) and time	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:23

S4	7	(oxidiz$4 near9 (layer or film) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold$4 or arm or support) and time and condensat$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:24
S5	6712	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:06
S6	143	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:07
S7	0	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and temperature and thermistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:09
S8	0	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and thermistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:11
S9	14	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and sensor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:11

S10	5	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and ((heat or thermal) same sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:26
S11	1	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and ((heat or thermal) same sensor) and graphite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:28
S12	0	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and ((heat or thermal) same sensor) and GaAs	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:34
S13	37	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and GaAs and graphite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:35
S14	3	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and GaAs and graphite and thermocouple	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:41
S15	3	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and GaAs and graphite and thermocouple and laser	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:41

S16	226127	(wafer or substrate or base or carrier or plate) near9 (holder or handler)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:34
S17	3428	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:36
S18	886	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:36
S19	23	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:58
S20	23	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:00

S21	10	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidat$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:04
S22	1	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature) and (record with temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:06
S23	1	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature) and record	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:08

S24	10	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:08
S25	5	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and ((holder or handler) with graphite)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:19
S26	1	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and ((holder or handler) with graphite) and (thermal near conductivity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:21
S27	190	((holder or handler) with graphite) and (thermal near conductivity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:21
S28	54	((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:22

S29	36	((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler) and (temperature with (holder or handler))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:22
S30	32	((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler) and (temperature with (holder or handler)) and (substrate or wafer or carrier or base or plate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:23
S31	210573	(substrate or wafer or carrier or base or plate or support) same oxidiz$4 anf (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near9 gas) and (time same oxidat $4) and temperature same (device or circuit) and (control same temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:04
S32	209648	(substrate or wafer or carrier or base or plate or support) same oxidiz$4 anf (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near9 gas) and (time same oxidat $4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:06

| S33 | 209639 | (substrate or wafer or carrier or base or plate or support) same oxidiz$4 anf (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near9 gas) and (time same oxidat $4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:06 |
| S34 | 209624 | (substrate or wafer or carrier or base or plate or support) same oxidiz$4 anf (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near9 gas) and (time same oxidat $4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) and ((gallium near arsenide) or "GaAs") and ((aluminum near arsenide) or "AlAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:08 |

S35	7	(substrate or wafer or carrier or base or plate or support) same oxidiz$4 and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near9 gas) and (time same oxidat $4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) and ((gallium near arsenide) or "GaAs") and ((aluminum near arsenide) or "AlAs")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:09
S36	110592	(thermocouple or pyrometer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:36
S37	37285	(thermocouple or pyrometer) same (device or circuit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:38
S38	590	(thermocouple or pyrometer) same (device or circuit) and (substrate or wafer or carrier or base or plate) same ("GaAs" or (gallium near arsenide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:41

S39	18	(thermocouple or pyrometer) same (device or circuit) and (substrate or wafer or carrier or base or plate) same ("GaAs" or (gallium near arsenide)) and (oxidiz$4 same ("GaAs" or (gallium near arsenide)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:43
S40	5	(thermocouple or pyrometer) same (device or circuit) and (substrate or wafer or carrier or base or plate) same ("GaAs" or (gallium near arsenide)) and (oxidiz$4 same ("GaAs" or (gallium near arsenide))) and graphite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 09:55
S41	1174	(438/770.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:22
S42	110	(438/770.ccls.) and (257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:32
S43	1354	(257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:32
S44	764	(257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.) and (oxidat$4 same (substrate or wafer or carrier or base or plate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:33

S45	362	(257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.) and (oxidat$4 same (substrate or wafer or carrier or base or plate)) and (oxidat$4 same gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:34
S46	257	(257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.) and (oxidat$4 same (substrate or wafer or carrier or base or plate)) and (oxidat$4 same gas) and (temperature near9 (substrate or wafer or carrier or base or plate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:40
S47	180	(257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.) and (oxidat$4 same (substrate or wafer or carrier or base or plate)) and (oxidat$4 same gas) and (temperature near9 (substrate or wafer or carrier or base or plate)) and (control$4 same temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:41
S48	1	(257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.) and (oxidat$4 same (substrate or wafer or carrier or base or plate)) and (oxidat$4 same gas) and (temperature near9 (substrate or carrier or	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:42

		base or plate)) and (control$4 same temperature) and vcsel				
S49	21	(257/E21.079, E21.082,E21.267, E21.282,E21.283, E21.284,E21.287, E21.291,E21.301. ccls.) and (oxidat$4 same (substrate or wafer or carrier or base or plate)) and (oxidat$4 same gas) and (temperature near9 (substrate or wafer or carrier or base or plate)) and (control$4 same temperature) and ((gallium near arsenide) or "GaAs")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:42
S50	861	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:50
S51	116480	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and ((gallium near arsenide) or "GaAs") or ((alumnium near arsenide) or "AlAs")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:51
S52	5	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and ((gallium near arsenide) or "GaAs") and ((alumnium near arsenide) or "AlAs")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:52

S53	49	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:53
S54	48	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer) and (circuit or device)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:54
S55	33	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:54
S56	21	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat$4 or oxidix$4) near9 gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:54

S57	20	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat$4 or oxidix$4) near9 gas) and (control$4 near9 temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:55
S58	19	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat$4 or oxidix$4) near9 gas) and (control$4 near9 temperature) and gas near9 (substrate or wafer or carrier or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:55
S59	1	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat$4 or oxidix$4) near9 gas) and (control$4 near9 temperature) and gas near9 (substrate or wafer or carrier or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:56

		and stack				
S60	19	438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz$4 or oxidat$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat$4 or oxidix$4) near9 gas) and (control$4 near9 temperature) and gas near9 (substrate or wafer or carrier or base) and (heat or thermal) near9 (substrate or wafer or carrier or base or plate or support)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 10:56
S61	5	(substrate or wafer or carrier or base or plate or support) same oxidiz$4 and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near9 gas) and (time same oxidat $4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) and ((gallium near arsenide) or "GaAs") and ((aluminum near arsenide) or "AlAs")	US-PGPUB	OR	ON	2008/09/16 11:05

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